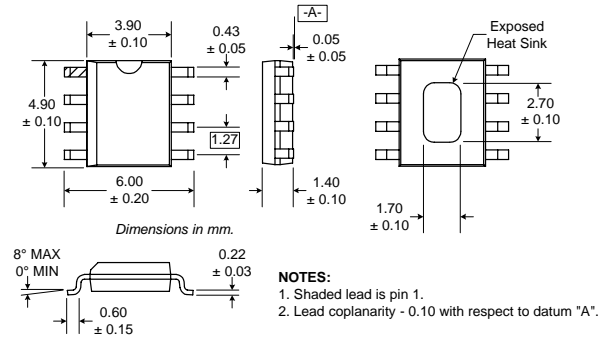


Typical Applications

- PCS Communication Systems
- Digital Communication Systems
- DECT Cordless Applications
- Commercial and Consumer Systems
- Portable Battery-Powered Equipment

Product Description

The RF2125P is a high power, high efficiency linear amplifier IC. The device is manufactured on an advanced Gallium Arsenide Heterojunction Bipolar Transistor (HBT) process and has been designed for use as the final RF amplifier in digital PCS phone transmitters and base stations requiring linear amplification operating between 1500MHz and 2200MHz. It will also function as a high efficiency amplifier for constant envelope applications such as DECT. The device is packaged in an 8-lead plastic package with a backside ground. The device is self-contained with the exception of the output matching network and power supply feed line. It produces a typical output power level of 1W.

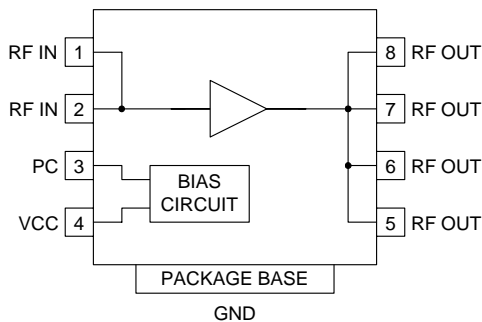


Optimum Technology Matching® Applied

- Si BJT       GaAs HBT       GaAs MESFET  
 Si Bi-CMOS       SiGe HBT       Si CMOS

Package Style: SOIC-8 Slug

- Features
- Single 2.7V to 7.5V Supply
  - 1W Output Power
  - 14dB Gain
  - 45% Efficiency
  - Power Down Mode
  - 1500MHz to 2200MHz Operation



Functional Block Diagram

Ordering Information

RF2125P High Power Linear Amplifier  
 RF2125P PCBA Fully Assembled Evaluation Board

RF Micro Devices, Inc.  
 7628 Thorndike Road  
 Greensboro, NC 27409, USA

Tel (336) 664 1233  
 Fax (336) 664 0454  
 http://www.rfmd.com

# RF2125P

## Absolute Maximum Ratings

Parameter	Rating	Unit
Supply Voltage ( $V_{CC}$ )	-0.5 to +7.5	$V_{DC}$
Power Control Voltage ( $V_{PC}$ )	-0.5 to +5V	V
DC Supply Current	450	mA
Input RF Power	+20	dBm
Output Load VSWR	20:1	
Operating Ambient Temperature	-40 to +85	°C
Storage Temperature	-40 to +100	°C

Refer to "Handling of PSOP and PSSOP Products" on page 16-15 for special handling information.



**Caution!** ESD sensitive device.

RF Micro Devices believes the furnished information is correct and accurate at the time of this printing. However, RF Micro Devices reserves the right to make changes to its products without notice. RF Micro Devices does not assume responsibility for the use of the described product(s).

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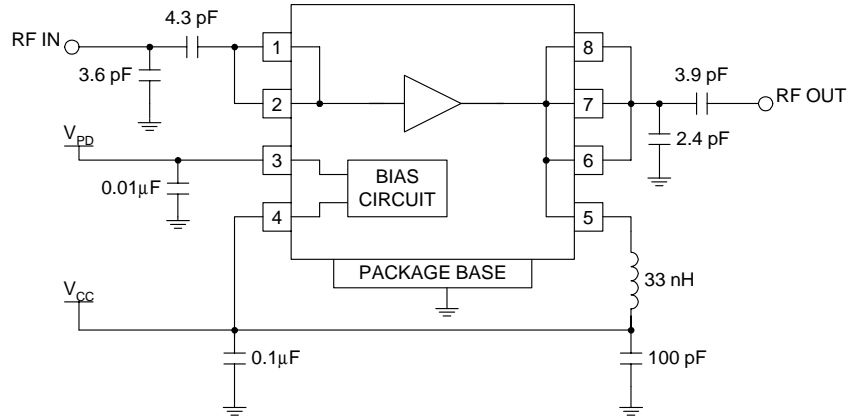
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Parameter	Specification			Unit	Condition
	Min.	Typ.	Max.		
<b>Overall</b>					$T=25^{\circ}\text{C}$ , $V_{CC}=6.0\text{V}$ , $V_{PC}=5.0\text{V}$ , $Z_{LOAD}=12\Omega$ , $P_{in} = 0\text{dBm}$ , Freq=1885MHz, Idle current=180mA
Frequency Range		1500 to 2200		MHz	
Maximum Output Power		+28.5		dBm	$V_{CC}=3.6\text{V}$ , $P_{IN}=+17\text{dBm}$
Maximum Output Power		+29.5		dBm	$V_{CC}=4.8\text{V}$ , $P_{IN}=+17\text{dBm}$
Maximum Output Power	+29.0	+30		dBm	$V_{CC}=6.0\text{V}$ , $P_{IN}=+17\text{dBm}$
Total Power Added Efficiency		45		%	Maximum output, $V_{CC}=3.6\text{V}$
Total Power Added Efficiency		45		%	Maximum output, $V_{CC}=4.8\text{V}$
Total Power Added Efficiency	40	45		%	Maximum output, $V_{CC}=6.0\text{V}$
Small-signal Gain	12	14		dB	
Second Harmonic		-40		dBc	
Third Harmonic		-45		dBc	
Fourth Harmonic		-35		dBc	
Isolation		15		dB	$V_{PC}=0.2\text{V}$
Input VSWR		1.5:1			With external matching network; see application schematic
<b>Two-tone Specification</b>					
Average Two-Tone Power		+27		dBm	PEP-3dB
$IM_3$	-23	-30		dBc	$P_{OUT}=+24\text{dBm}$ for each tone
$IM_5$		-35		dBc	$P_{OUT}=+24\text{dBm}$ for each tone
$IM_7$		-45		dBc	$P_{OUT}=+24\text{dBm}$ for each tone
<b>Power Control</b>					
$V_{PC}$	1.5	3.3	3.5	V	To obtain 180mA idle current
PC Current		1		mA	$V_{PC}=2.0\text{V}$
		2		mA	$V_{PC}=3.5\text{V}$
Power Control "OFF"	0.2	0.5		V	Threshold voltage at device input
<b>Power Supply</b>					
Power Supply voltage		2.7 to 7.5		V	
Supply Current	200	360	500	mA	$P_{OUT}=+30\text{dBm}$ , $V_{CC}=6.0\text{V}$
Power Down Current		0.5	10	$\mu\text{A}$	$V_{PC}=0.2\text{V}$

Pin	Function	Description	Interface Schematic
1	<b>RF IN</b>	RF input. This input is DC coupled, so an external blocking capacitor is required if this pin is connected to a DC path. An optimum match to 50 $\Omega$ is obtained by providing an external series capacitor of 4.3pF and then a shunt capacitor of 3.3pF; see the application schematic. Those values are typical for 1880MHz; other values may be required for other frequencies.	
2	<b>RF IN</b>	Same as pin 1.	
3	<b>PC</b>	Power control pin. For obtaining maximum performance the voltage on this pin can be used to set correct bias level. In a typical application this is implemented by a feedback loop. The feedback can be based on the actual supply current of the device, i.e. maintaining a fixed current level, or it can be based on the RF output power level to maintain a fixed RF power level (Automatic Level Control loop). A voltage of 0.5V or lower brings the part into power down state.	
4	<b>VCC</b>	Power supply pin for the bias circuits. External low frequency bypass capacitors should be connected if no other low frequency decoupling is nearby.	
5	<b>RF OUT</b>	RF output and bias for the output stage. The power supply for the output transistor needs to be supplied to this pin. This can be done through a quarter wave length microstrip line that is RF grounded at the other end, or through an RF inductor that supports the required DC currents. Optimum load impedance is achieved by providing a shunt capacitor of 3.0pF and a series capacitor of 3.9pF; see the application schematic. Those values are typical for 1880MHz; other values may be required for other frequencies. Since there are several output pins available, which are internally connected, one pin can be used for connecting the bias, another for connecting a (third) harmonic trap filter, and the other pins for the RF output.	
6	<b>RF OUT</b>	Same as pin 5.	
7	<b>RF OUT</b>	Same as pin 5.	
8	<b>RF OUT</b>	Same as pin 5.	
<b>Pkg Base</b>	<b>GND</b>	Ground connection. The backside of the package should be connected to the ground plane through a short path, i.e., vias under the device may be required.	

# RF2125P

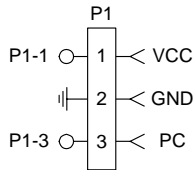
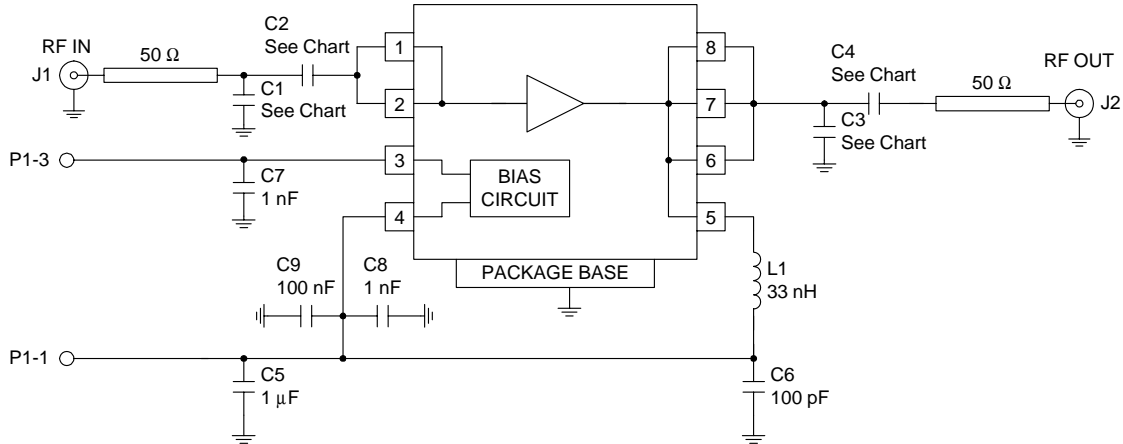
## Application Schematic 1880MHz Operation



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## Evaluation Board Schematic (Download [Bill of Materials](http://www.rfmd.com) from www.rfmd.com.)



2125402 Rev -

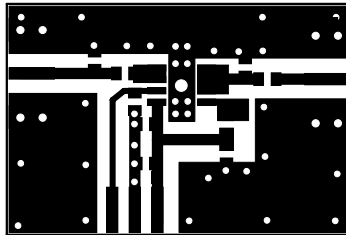
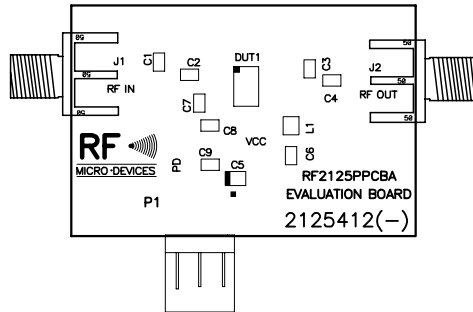
Capacitors are ATC type.  
The 2.7 pF capacitor is 2.4 pF in parallel with 0.3 pF.

APPLICATION	C1 (pF)	C2 (pF)	C3 (pF)	C4 (pF)
DCS1800 (1710 to 1785 MHz)	3.3	7.5	3.6	3.9
DECT (1880 to 1990 MHz)	3.0	3.9	2.7	3.6
Broadband and Unlicensed PCS (1850 to 1910 MHz)	3.6	4.3	2.4	3.9
Broadband and Unlicensed PCS (1910 to 1970 MHz)	3.0	3.9	2.7	3.6

# RF2125P

## Evaluation Board Layout 1.0" x 1.5"

Board Thickness 0.031"; Board Material FR-4



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